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**AMENDMENTS TO THE CLAIMS**

1. (cancelled)

2. (cancelled)

4. (cancelled)

5. (cancelled)

6. (cancelled)

7. (cancelled)

8. (cancelled)

9. (cancelled)

10. (cancelled)

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14. (cancelled)

15. (cancelled)

17. (cancelled)

23. (cancelled)

24. (currently amended) The method of claim 23 52, wherein the step of trimming the polysilicon portion comprises trimming only a portion of the polysilicon portion.

36. (currently amended) A method for forming selectively compensated semiconductor devices comprising the steps of:

forming a plurality of polysilicon portions of gate conductors on a substrate having a semiconductor portion;

masking at least one polysilicon portion intended for a n-channel device;

trimming at least an electrically significant portion of one unmasked polysilicon portion intended for a p-channel device by a film growth method selective to laser-absorbing polysilicon, wherein the extent of trimming is selected to accomplish device compensation of the p-channel and n-channel devices; and

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wherein the trimming film is anisotropically etched, forming gate conductor spacers.

37. (previously added) The method of claim 36, wherein the selective film growth method comprises selective surface nitridation.

38. (previously added) The method of claim 37, wherein trimming comprises reacting the polysilicon portion to a depth of at least ten nanometers.

39. (previously added) The method of claim 37, wherein the step of trimming the gate conductor by selective surface nitridation comprises exposing structures formed on the semiconductor portion to about 150 expose pulses of 308 nm laser irradiation with an energy fluence of 400-500 mJ/cm<sup>2</sup> in the presence of ammonia at a pressure of about 300-500 torr.

40. (previously added) The method of claim 36, wherein the step of trimming the gate conductor comprises exposing polysilicon to laser irradiation of 308 nanometer wavelength.

41. (cancelled)

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42. (cancelled)

43. (currently amended) The method of claim ~~23~~ 52, wherein trimming at least an electrically significant portion of the polysilicon portion comprises reacting the polysilicon portion to a depth of at least ten nanometers.

44. (currently amended) The method of claim ~~23~~ 52, wherein trimming at least an electrically significant portion of the polysilicon portion comprises reacting the polysilicon portion to a depth within a range of 10 to 100 nanometers.

45. (currently amended) The method of claim ~~23~~ 52, wherein the selective film growth method comprises selective surface nitridation.

46. (currently amended) The method of claim ~~27~~ 45, wherein the step of trimming the gate conductor by selective surface nitridation comprises exposing structures formed on the semiconductor portoin to 50-1000 expose pulses of laser irradiation with an energy fluence of 200-700 mJ/cm<sup>2</sup> in the presence of ammonia at a pressure of 10-1500 torr.

47. (currently amended) The method of claim ~~28~~ 46, wherein the laser irradiation is of a wavelength absorbed by the gate material selective to surrounding materials.

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48. (currently amended) The method of claim ~~28~~ 46, wherein the step of trimming the gate conductor by selective surface nitridation comprises exposing structures formed on the semiconductor portion to about 150 expose pulses of 308 nm laser irradiation with an energy fluence of 400-500 mJ/cm<sup>2</sup> in the presence of ammonia at a pressure of about 300-500 torr.

49. (currently amended) The method of claim ~~30~~ 48, wherein ammonia is supplied at about 100 ccm/min.

50. (currently amended) The method of claim ~~23~~ 52, wherein the step of trimming at least an electrically significant portion of the polysilicon portion further comprises selectively compensating n-channel and p-channel devices.

51. (currently amended) The method of claim ~~23~~ 52, additionally comprising the step of at least partially removing the trimming film.

52. (currently amended) ~~The~~ A method of claim 23 for forming a trimmed gate in a transistor comprising the steps of:

forming a polysilicon portion of a gate conductor on a substrate having a semiconductor portion; and

trimming at least an electrically significant portion of the polysilicon portion

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by a film growth method selective to laser-absorbing semiconductor material;

and

wherein the trimming film is anisotropically etched, forming gate conductor spacers.

53. (currently amended) ~~The A method of claim 23 for forming a trimmed gate in a transistor comprising the steps of:~~

forming a polysilicon portion of a gate conductor on a substrate having a semiconductor portion; and

trimming at least an electrically significant portion of the polysilicon portion by a film growth method selective to laser-absorbing semiconductor material;

and

wherein the trimming film is silicon-rich and the method further comprises the step of forming additional nitride or oxide layers on the trimming film.